

SIPR-7120

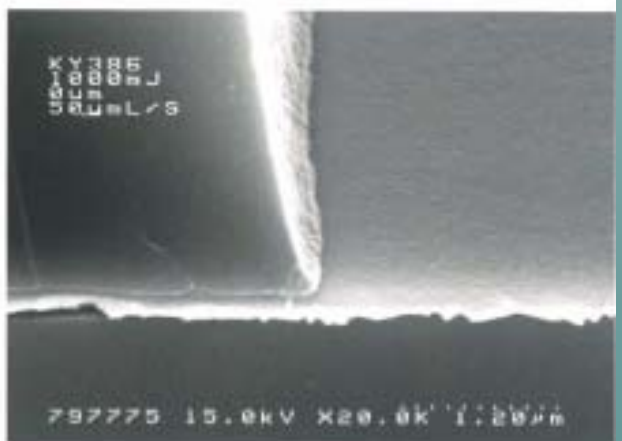
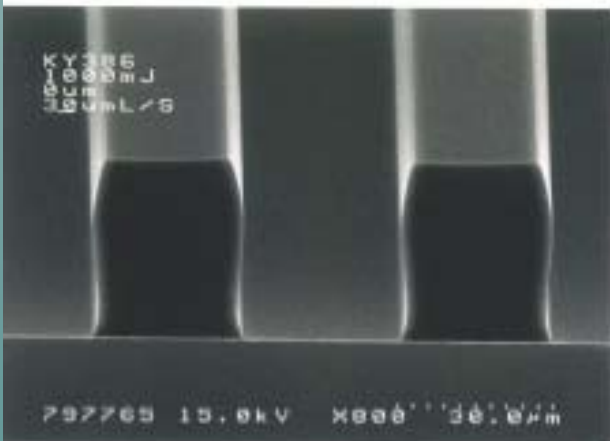
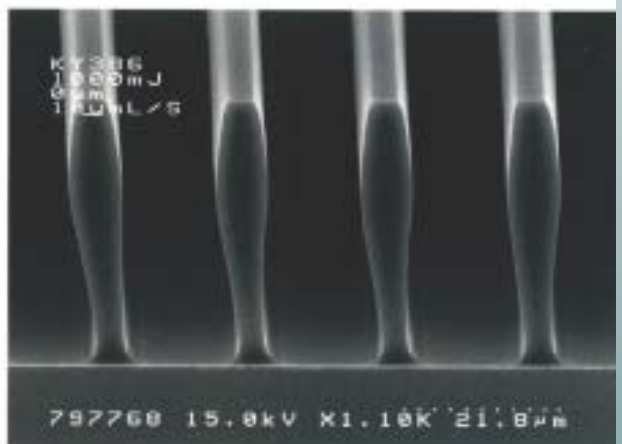
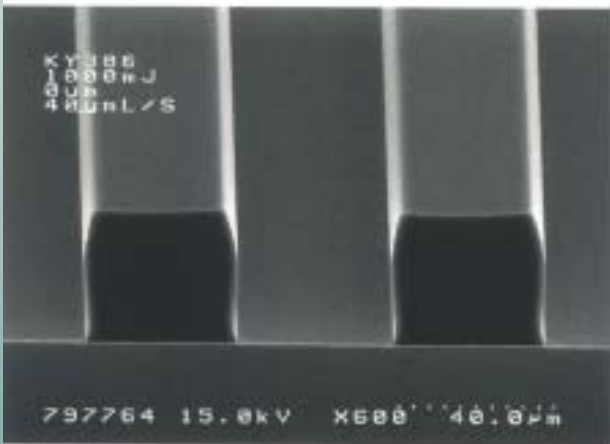
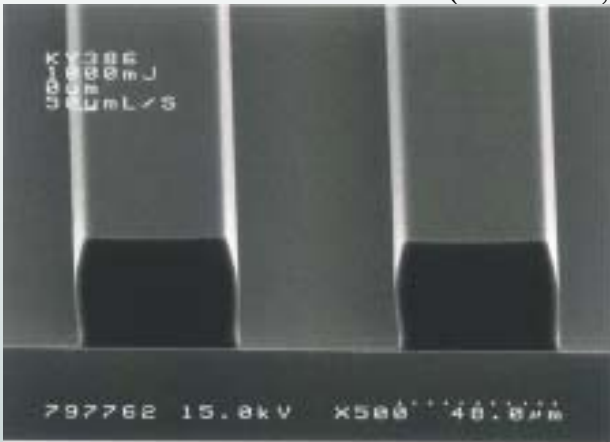
Cu

Sputtering Substrate



PEB 80°C x 120sec

Thickness : 45μm Prebake : 130°C x 300sec Dev : AZ-400K:H₂O(1:3)50sec x12 puddles
Exposure : NIKON NSR1755i7A (NA=0.50, σ=0.60); 1000mJ



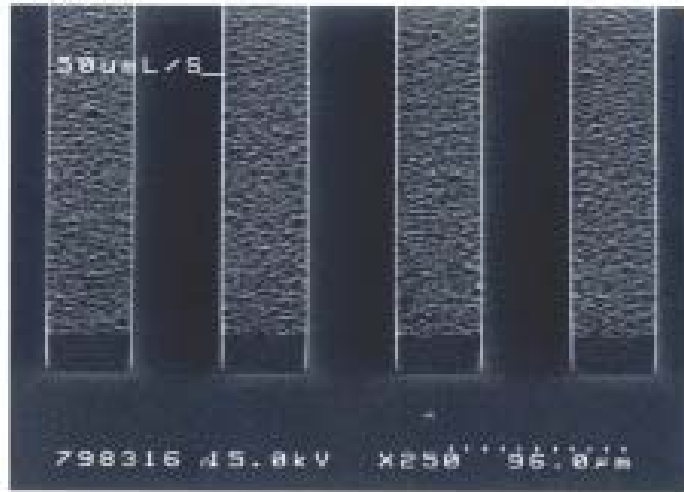
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Cu Sputtered On Si

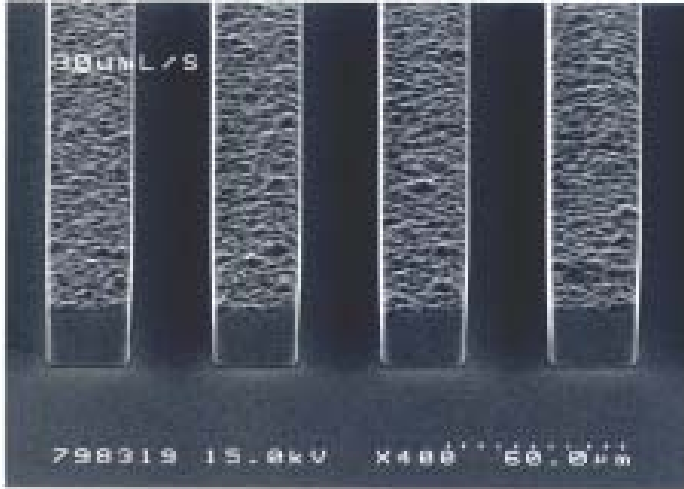


Exposure : NIKON NSR1755i7A (NA=0.50, $\sigma=0.60$); 1000mJ Focus : 0 μ m
O₂RIE : 100W x 30sec. (50Pa, O₂flow=200sccm)
Cu Plating : 100mA x 40min. @ Room Temp. (MICROFAB Cu200)

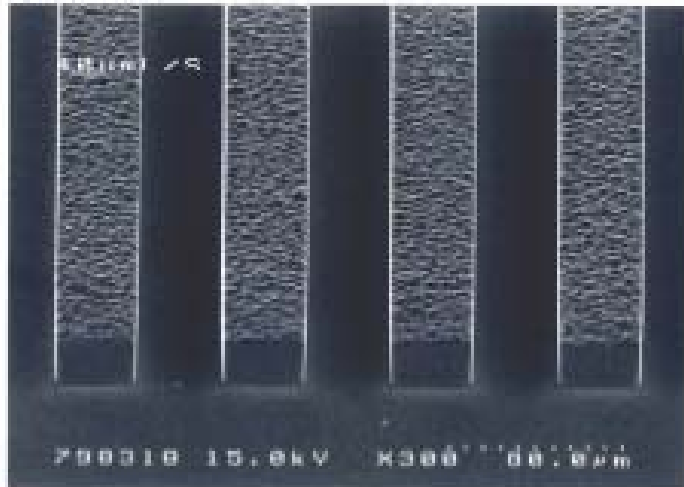
50 μ m L/S



30 μ m L/S



40 μ m L/S



20 μ m L/S

